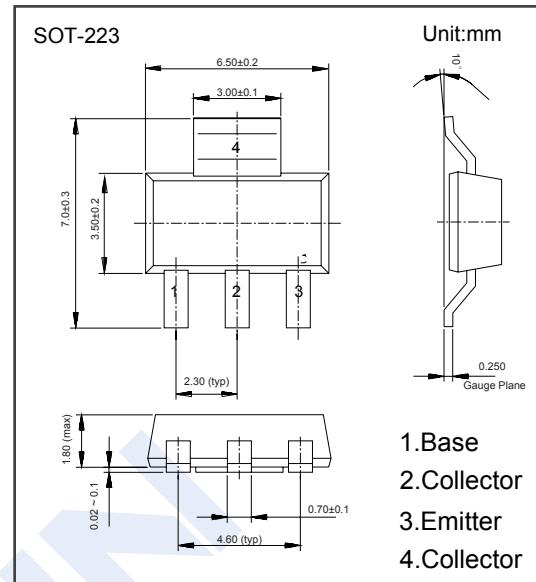
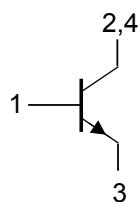


NPN Transistors**BCP68 (KCP68)****■ Features**

- High current (max. 1 A)
- Low voltage (max. 20 V)
- Complements to BCP69

**■ Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	32	V
Collector - Emitter Voltage	V _{CEO}	20	
Emitter - Base Voltage	V _{EBO}	5	
Collector Current - Continuous	I _C	1	A
Collector Current - Pulse	I _{CP}	2	
Base Current - Pulse	I _{BP}	0.2	
Collector Power Dissipation	P _C	1.37	W
Thermal Resistance from Junction to Ambient	R _{θJA}	91	°C/W
Thermal Resistance from Junction to Soldering Point	R _{θJS}	10	
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-65 to 150	

NPN Transistors

BCP68 (KCP68)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100 \mu A, I_E = 0$	32			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 mA, I_B = 0$	20			V
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu A, I_C = 0$	5			V
Collector-base cut-off current	I_{CBO}	$V_{CB} = 25 V, I_E = 0$			100	nA
		$V_{CB} = 25 V, I_E = 0, T_J = 150^\circ C$			10	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			100	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1 A, I_B = 100mA$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 1 A, I_B = 100mA$			1.2	V
Base - emitter voltage	V_{BE}	$V_{CE} = 10V, I_C = 5mA$		0.62		
		$V_{CE} = 1V, I_C = 1 A$			1	
DC current gain	h_{FE}	$V_{CE} = 10V, I_C = 5mA$	50			
		$V_{CE} = 1V, I_C = 500mA$	85		375	
		$V_{CE} = 1V, I_C = 1 A$	60			
Collector capacitance	C_{ob}	$V_{CB} = 5V, I_E = I_E = 0, f = 1MHz$		38		pF
Transition frequency	f_T	$V_{CE} = 5V, I_C = 10mA, f = 100MHz$	40			MHz

■ Classification of $h_{FE}(2)$

Type	BCP68	BCP68-16	BCP68-25
Range	85-375	100-250	160-375
Marking	BCP68	BCP68-16	BCP68-25

■ Typical Characteristics

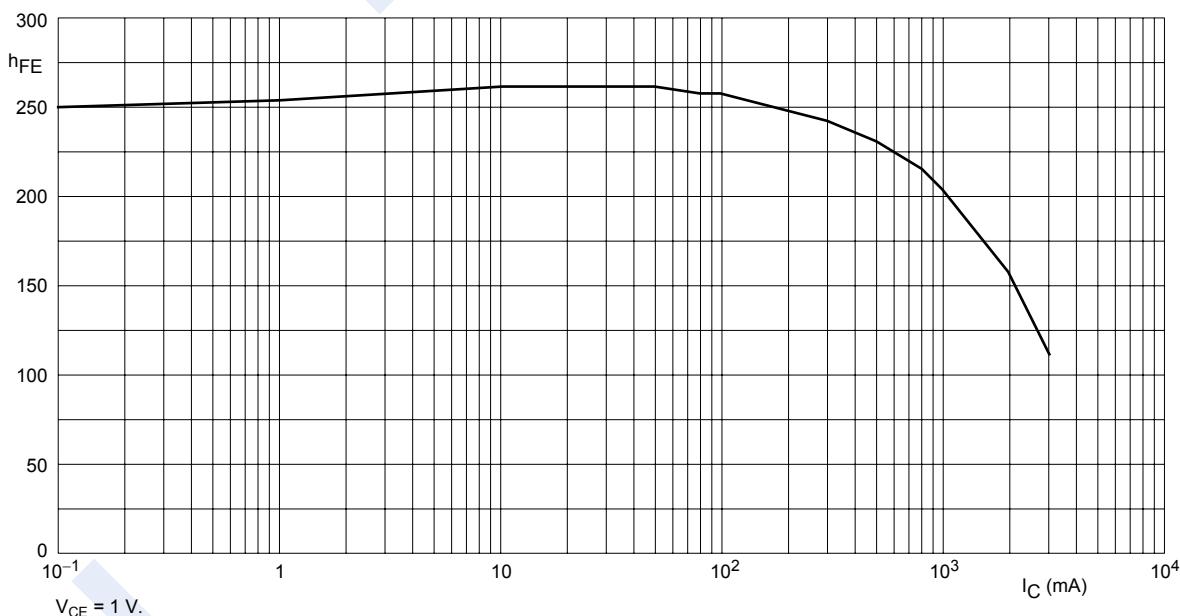


Fig.1 DC current gain; typical values.